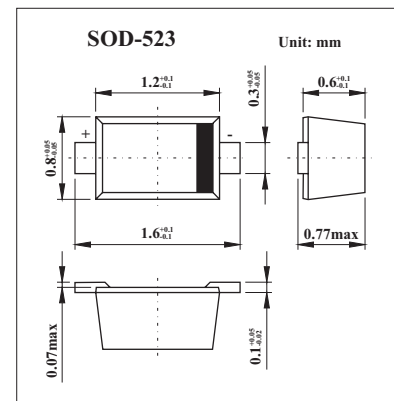


## Silicon Schottky Barrier Diode

## HSC276

## ■ Features

- High forward current, Low capacitance.
- Ultra small Flat Package (UFP) is suitable for surface mount design.

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	3	V
Average rectified current	$I_o$	30	mA
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse voltage	$V_R$	$I_R = 10 \mu\text{A}$	30			V
Reverse current	$I_R$	$V_R = 0.5\text{V}$			0.5	$\mu\text{A}$
Forward voltage	$I_F$	$V_R = 0.5\text{V}$	35			mA
Capacitance	C	$V_R = 0.5\text{V}, f = 1\text{MHz}$			0.85	pF
ESD-Capability (Note 1)		C=200pF, Both forward and reverse direction 1 pulse.	30			V

## Note

1. Failure criterion ;  $I_R \geq 100\text{mA}$  at  $V_R = 0.5\text{V}$

## ■ Marking

Marking	C2
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